

#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BVsss	Rss(on) Typ	Is Max TA = +25°C
24V	$7.4 \text{m}\Omega$ @ $V_{GS} = 3.8 \text{V}$	13.0A

### **Description**

This new generation MOSFET is designed to minimize the on-state resistance (Rss(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Battery Management
- Load Switch
- **Battery Protection**

### **Features**

- CSP with Footprint 2.70mm × 1.81mm
- Height = 0.21mm for Low Profile
- **ESD Protection of Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

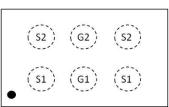
#### **Mechanical Data**

- Case: X3-DSN2718-6
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu or NiAu. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0026 grams (Approximate)

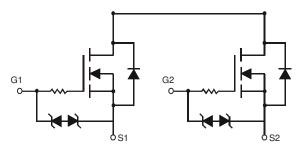




**ESD PROTECTED** 



Top View



**Equivalent Circuit** 

### **Ordering Information** (Note 4)

Ī	Part Number	Case	Packaging
	DMN2012UCA6-7	X3-DSN2718-6	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



M3 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: G = 2019) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Kev

Date Code No	y											
Year	2018	2019	20	020	2021	2022	2	2023	2024	20:	25	2026
Code	F	G		Н	1	J		K	L	N	1	N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characterist	Symbol	Value	Unit			
Source-Source Voltage	Source-Source Voltage					
Gate-Source Voltage			Vgss	±12	V	
Continuous Course Current (Note E) V 4 EV	Ctoody Ctoto	T <sub>A</sub> = +25°C	I-	13.0	Α	
Continuous Source Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +70°C	Is	10.4		
Continuous Course Courset (Note 5) V	Ctoody Ctoto	T <sub>A</sub> = +25°C	1	10.8	А	
Continuous Source Current (Note 5) V <sub>GS</sub> = 2.5V	Steady State	T <sub>A</sub> = +70°C	Is	8.6		
Pulsed Source Current (Note 6)	I <sub>SM</sub>	60	Α			

# **Thermal Characteristics**

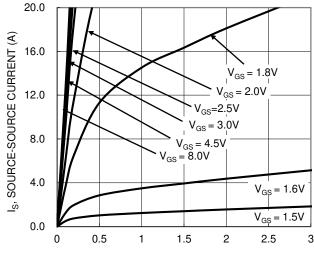
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P <sub>D</sub>	0.82	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7)	Reja	151.9	°C/W
Power Dissipation (Note 5)	PD	2.3	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	Reja	55.0	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Source-Source Breakdown Voltage	BVsss	24	_		V	$V_{GS} = 0V$ , $I_{S} = 1mA$	
Zero Gate Voltage Source Current $T_J = +25$ °C	I <sub>SSS</sub>	_	_	1	μΑ	$V_{SS} = 20V$ , $V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 12V, V_{SS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	0.9	1.3	V	$V_{SS} = 10V$ , $I_{S} = 1mA$	
		_	7.0	9.0		V <sub>G</sub> S = 4.5V, I <sub>S</sub> = 5A	
		_	7.3	9.5		$V_{GS} = 4.0V, I_{S} = 5A$	
Static Source-Source On-Resistance	Rss(on)		7.4	10.1	mΩ	V <sub>G</sub> S = 3.8V, I <sub>S</sub> = 5A	
	, ,	_	7.9	10.3		V <sub>GS</sub> = 3.1V, I <sub>S</sub> = 5A	
		_	9.1	13.0		V <sub>GS</sub> = 2.5V, I <sub>S</sub> = 5A	
Diode Forward Voltage	Vss	_	0.7	_	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 10A	
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance	Ciss	_	2417	_			
Output Capacitance	Coss	_	270	_	pF	$V_{SS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	102	_		1 = 1.0WHZ	
Total Gate Charge	Qg	_	26.0	_			
Gate-Source Charge	Q <sub>gs</sub>	_	5.2	_	nC	$V_{SS} = 19.2V, V_{GS} = 4.0V,$	
Gate-Drain Charge	Qgd	_	9.5	_	IIC	Is = 3A	
Gate Charge at VTH	Q <sub>g</sub> (TH)	_	4.5	_			
Turn-On Delay Time	t <sub>D</sub> (ON)	_	<b>—</b> 543				
Turn-On Rise Time	tR	_	1183	_		Vss = 20V, Vgs = 4.0V,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	1810	_	ns	$I_S = 10A, R_g = 6.0\Omega$	
Turn-Off Fall Time	tF	_	1602	_			

- 5. Device mounted on FR-4 material with 1inch2 (6.45cm2), 2oz. (0.071mm thick) Cu.
- Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- 8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to production testing.







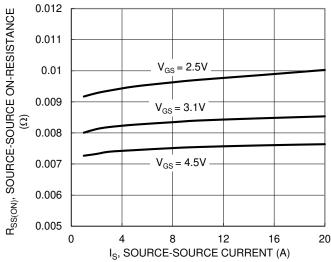


Figure 3. Typical On-Resistance vs. Source Current and Gate Voltage

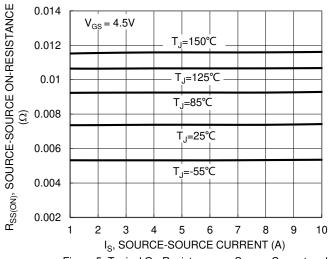
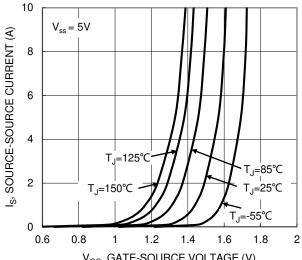


Figure 5. Typical On-Resistance vs. Source Current and Junction Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

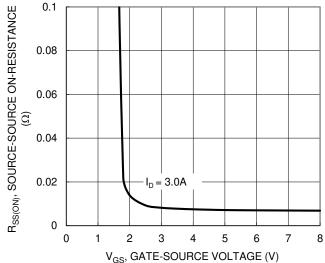


Figure 4. Typical Transfer Characteristic

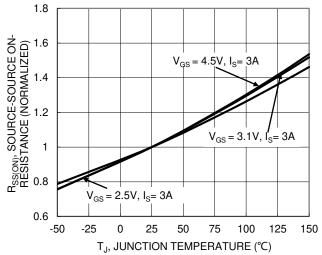


Figure 6. On-Resistance Variation with Junction Temperature



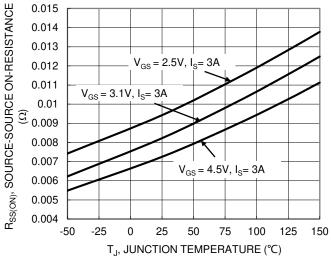
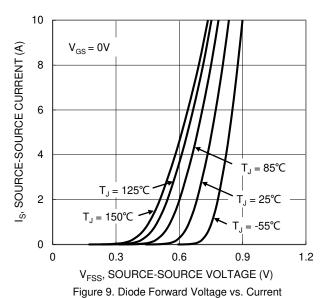


Figure 7. On-Resistance Variation with Junction Temperature



10 8 6 S 9 4 V<sub>SS</sub> = 10V, I<sub>S</sub> = 13A 2 0 0 10 20 30 40 50 60

Qg (nC) Figure 11. Gate Charge

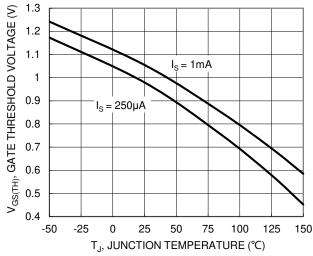


Figure 8. Gate Threshold Variation vs. Junction Temperature

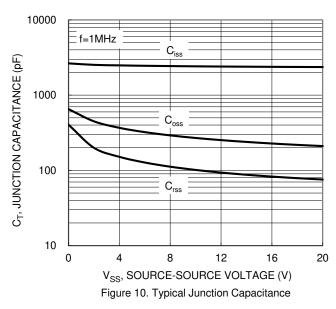


Figure 12. SOA, Safe Operation Area



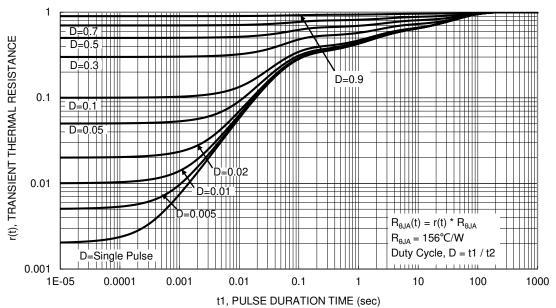


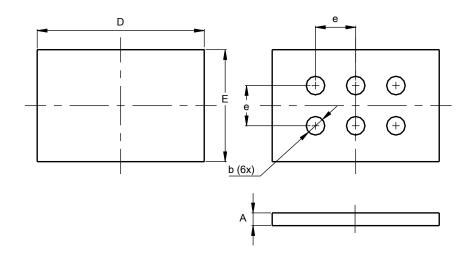
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

### X3-DSN2718-6

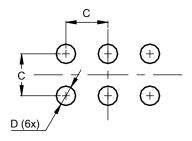


X3-DSN2718-6							
Dim Min Max Typ							
Α	0.16	0.26	0.21				
b	0.27	0.33	0.30				
D	2.65	2.75	2.70				
Е	1.86	1.81					
e 0.62 0.68 0.65							
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### X3-DSN2718-6



Dimensions	Value (in mm)		
С	0.65		
D	0.30		



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